

SAMSUNG SEMICONDUCTOR INC

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KSR2014

PNP EPITAXIAL SILICON TRANSISTOR

T-37-13

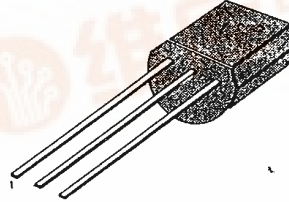
SWITCHING APPLICATION (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit Driver circuit
- Built in bias Resistor ($R_1 = 4.7K\Omega$, $R_2 = 47K\Omega$)
- Complement to KSR1014

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-100	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ\text{C}$

TO-92

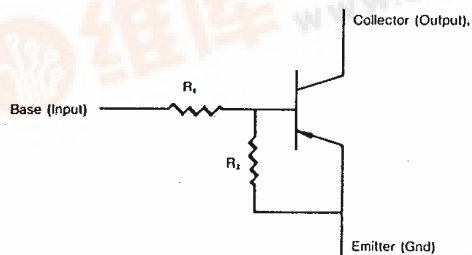


1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -10\mu\text{A}$, $I_E = 0$	-50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -100\mu\text{A}$, $I_B = 0$	-50			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -40\text{V}$, $I_E = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -5\text{mA}$	68			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}$, $I_B = -0.5\text{mA}$			-0.3	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = -5\text{mA}$, $I_C = -10\text{V}$		200		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$ $f = 1.0\text{MHz}$		5.5		pF
Input Off Voltage	$V_i(off)$	$V_{CE} = -5\text{V}$, $I_C = -100\mu\text{A}$	-0.5			V
Input On Voltage	$V_i(on)$	$V_{CE} = -0.2\text{V}$, $I_C = -5\text{mA}$			-1.3	V
Input Resistor	R_1		3.2	4.7	6.2	$K\Omega$
Resistor Ratio	R_1/R_2		0.09	0.1	0.11	

Equivalent Circuit



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